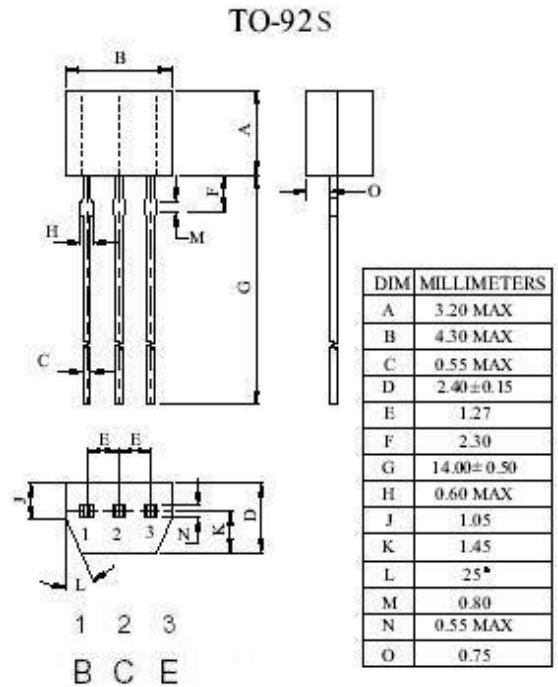


■ ■ APPLICATION: Switching application, Amplifier application.

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	6	V
Collector current	I _c	0.2	A
Collector current	I _{cp}	0.4	A
Collector Power Dissipation	P _c	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C, R_G=10KΩ)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{cbo}	60			V	I _c =50uA	I _e =0	
Collector-Emitter Breakdown Voltage	BV _{ceo}	50			V	I _c =1mA	I _b =0	
Emitter-Base Breakdown Voltage	BV _{ebo}	6			V	I _e =50uA	I _c =0	
Collector Cut-off Current	I _{cbo}			0.1	uA	V _{cb} =50V	I _e =0	
Emitter Cut-off Current	I _{ebo}			0.1	uA	V _{eb} =5V	I _c =0	
Base-Emitter Saturation Voltage	V _{be(sat)}			1	V	I _c =100mA	I _b =10mA	
Collector-Emitter Saturation Voltage	V _{ce(sat)}			0.3	β	I _c =100mA	I _b =10mA	
DC Current Gain	h _{FE}	100		800	β值	V _{ce} =6V	I _c =1mA	
Gain bandwidth product	f _T		200		MHz	V _{ce} =6V	I _c =10mA	
Common Base Output Capacitance	C _{ob}		3		pF	V _{cb} =10V	I _e =0	f=1MHz

■ ■ h_{FE} Classification And Marking

Print Mark	C3330S				
Classification	R	S	T	U	V
h _{FE}	100~200	140~280	200~400	280~560	400~800